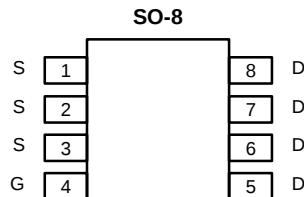




N-Channel 30-V (D-S) MOSFET

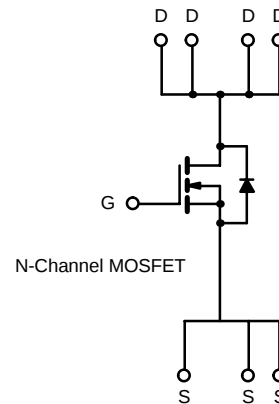
TrenchFET®
Power MOSFETs

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.024 @ $V_{GS} = 10$ V	8
	0.035 @ $V_{GS} = 4.5$ V	6.6



Top View

Ordering Information: Si4412ADY
Si4412ADY-T1 (with Tape and Reel)



ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V _{DS}	30		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _J = 150°C) ^a	T _A = 25°C	I _D	8	5.8	A
	T _A = 70°C		6.4	4.6	
Pulsed Drain Current (10 μs Pulse Width)		I _{DM}	30		
Continuous Source Current (Diode Conduction) ^a		I _S	2.3	1.2	W
Maximum Power Dissipation ^a	T _A = 25°C	P _D	2.5	1.3	
	T _A = 70°C		1.6	0.8	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	R_{thJA}	45	50	$^\circ\text{C/W}$
	Steady State		80	95	
Maximum Junction-to-Foot	Steady State	R_{thJF}	16	20	

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

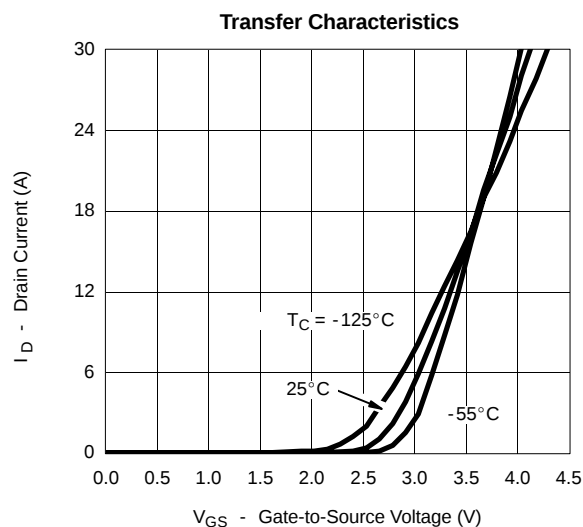
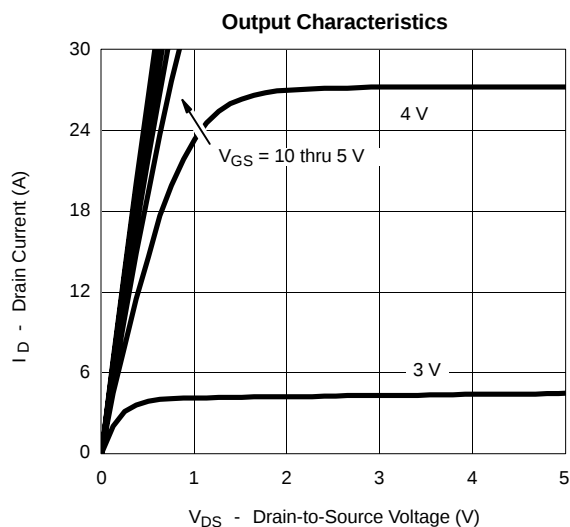
SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1.0			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 20\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\ \text{V}, V_{GS} = 0\ \text{V}$			1	μA
		$V_{DS} = 30\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 55^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}, V_{GS} = 10\ \text{V}$	30			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\ \text{V}, I_D = 8\ \text{A}$		0.020	0.024	Ω
		$V_{GS} = 4.5\ \text{V}, I_D = 6.6\ \text{A}$		0.029	0.035	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\ \text{V}, I_D = 8\ \text{A}$		21		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.3\ \text{A}, V_{GS} = 0\ \text{V}$		0.75	1.1	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 15\ \text{V}, V_{GS} = 10\ \text{V}, I_D = 2\ \text{A}$		16	20	nC
Gate-Source Charge	Q_{gs}			3		
Gate-Drain Charge	Q_{gd}			1.5		
Gate Resistance	R_g		0.5		2.0	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\ \text{V}, R_L = 15\ \Omega$ $I_D \cong 1\ \text{A}, V_{GEN} = 10\ \text{V}, R_G = 6\ \Omega$		15	20	ns
Rise Time	t_r			6	12	
Turn-Off Delay Time	$t_{d(off)}$			26	50	
Fall Time	t_f			10	20	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.3\ \text{A}, di/dt = 100\ \text{A}/\mu\text{s}$		40	80	

Notes

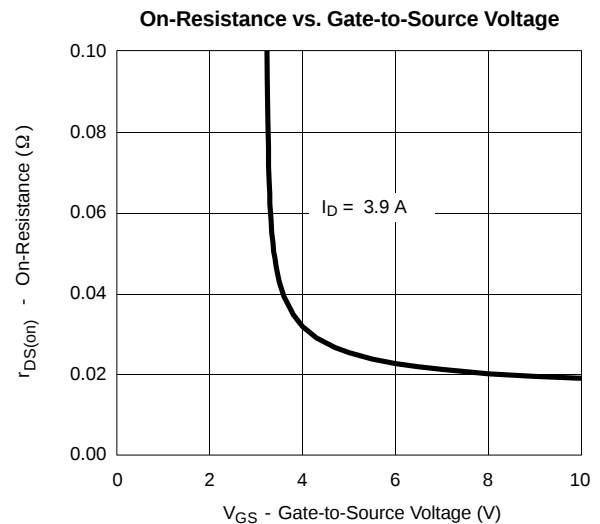
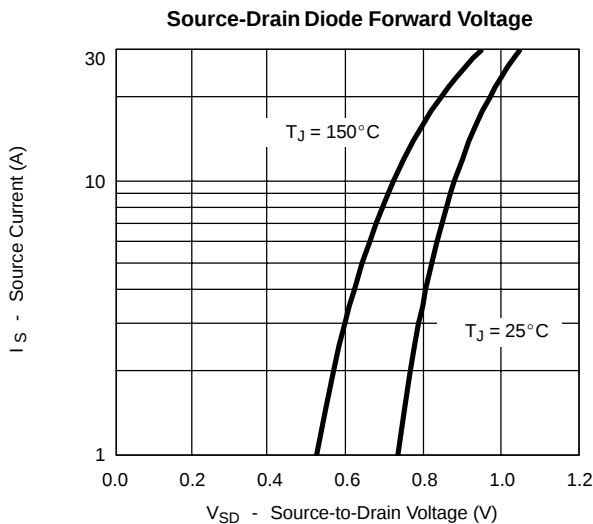
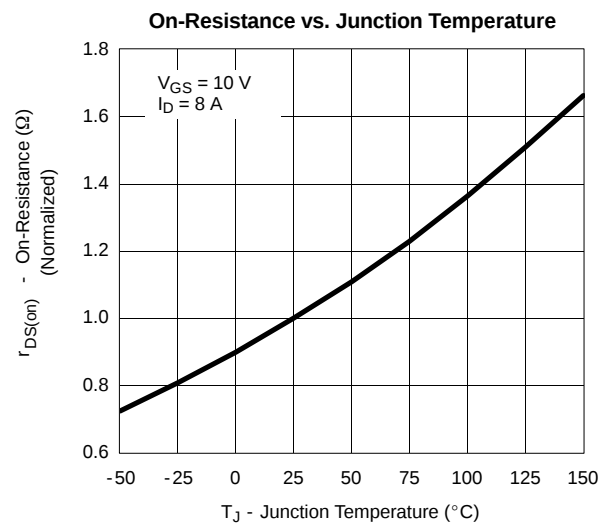
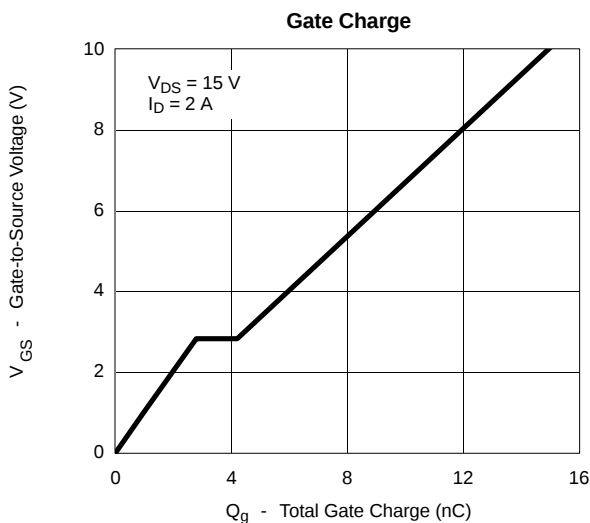
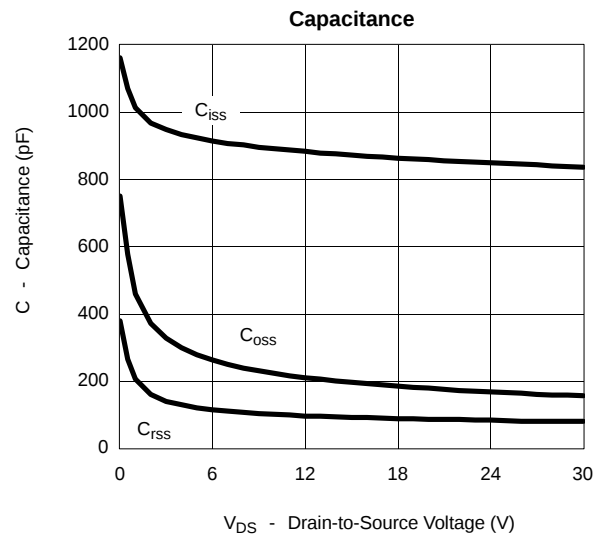
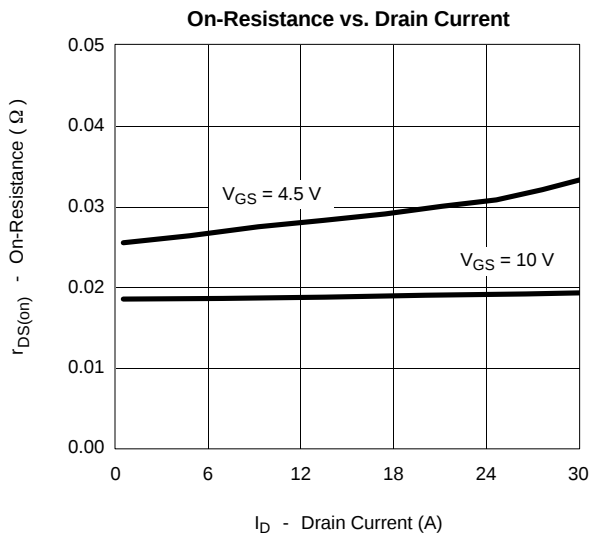
- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

